



N-channel 150V, 11mΩ, 120A, TO-220 Trench Power MOSFET 溝槽式功率場效應管

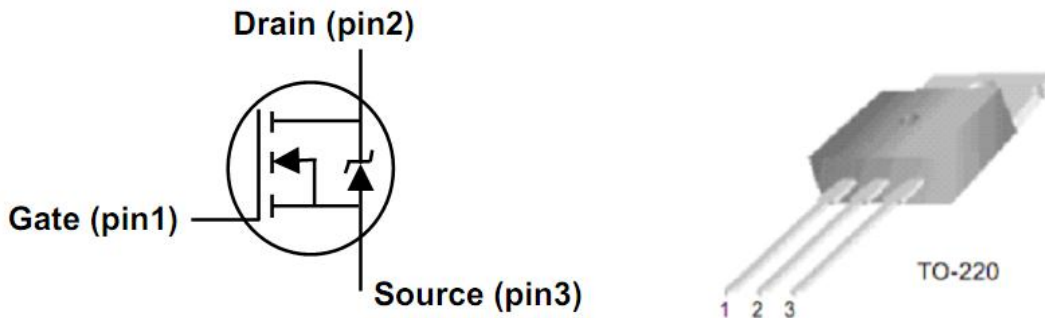
■ **Features 特點**

- Advanced trench technology 优秀沟槽技术
- Ultra low on-resistance 超低導通電阻
- Low gate charge 低柵電荷密度
- Fast switching 快速開關能力
- High operating temperature 高工作溫度範圍

■ **Applications 應用**

- Switch mode power supplies 開關電源
- DC-DC converters and UPS 直流直流變換和不間斷電源
- PWM motor controls 脈寬調製電機控制
- General switching applications 普通開關應用

■ **Internal Schematic Diagram 內部結構**



■ **Absolute Maximum Ratings 最大額定值**

Characteristic 特性參數	Symbol 符號	Rat 額定值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	BV_{DSS}	150	V
Gate- Source Voltage 柵極-源極電壓	V_{GS}	+25	V
Drain Current (continuous)漏極電流-連續	I_D (at $T_C = 25^\circ C$ at $T_C = 100^\circ C$)	120 85	A
Drain Current (pulsed)漏極電流-脈沖	I_{DM}	480	A
Total Device Dissipation 總耗散功率	$P_{TOT}(at T_C = 25^\circ C)$	350	W
Single Pulse Avalanche Energy 雪崩能量	E_{AS}	552	mJ
Thermal Resistance Junction-Case 熱阻	$R_{\theta JC}$	0.4	$^\circ C/W$
Junction/Storage Temperature 結溫/儲存溫度	T_J, T_{stg}	-55~175	$^\circ C$



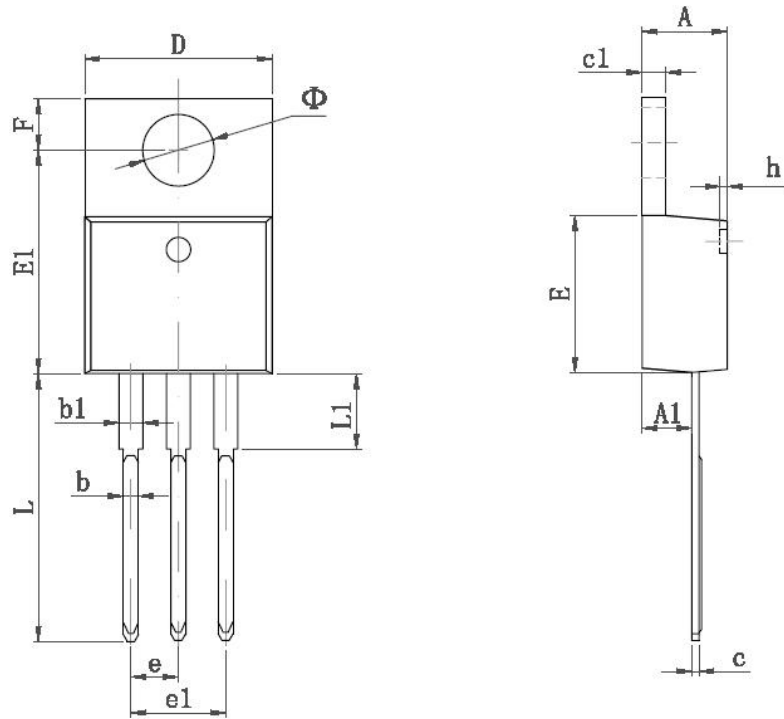
■ Electrical Characteristics 電特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如無特殊說明，溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓($I_D=250\mu\text{A}, V_{GS}=0\text{V}$)	BV_{DSS}	150	—	—	V
Gate Threshold Voltage 柵極開啓電壓($I_D=250\mu\text{A}, V_{GS}=V_{DS}$)	$V_{GS(th)}$	2	—	4	V
Zero Gate Voltage Drain Current 零柵壓漏極電流($V_{GS}=0\text{V}, V_{DS}=150\text{V}$)	I_{DSS}	—	—	1	μA
Gate Body Leakage 柵極漏電流($V_{GS}=\pm 25\text{V}, V_{DS}=0\text{V}$)	I_{GSS}	—	—	± 100	nA
Static Drain-Source On-State Resistance 静态漏源導通電阻($I_D=60\text{A}, V_{GS}=10\text{V}$)	$R_{DS(ON)}$	—	10	11	$\text{m}\Omega$
Source Drain Current 源極-漏極電流	I_{SD}	—	—	120	A
Source Drain Current (pulsed) 源極-漏極電流(脈沖)	I_{SDM}	—	—	380	A
Diode Forward Voltage Drop 內附二極管正向壓降($I_{SD}=60\text{A}, V_{GS}=0\text{V}$)	V_{SD}	—	—	1.2	V
Gate Resistance 柵極電阻 ($V_{GS}=0\text{V}, V_{DS}=50\text{V}, f=1\text{MHz}$)	R_g	—	1.5	—	Ω
Input Capacitance 輸入電容 ($V_{GS}=0\text{V}, V_{DS}=75\text{V}, f=1\text{MHz}$)	C_{ISS}	—	—	4900	pF
Common Source Output Capacitance 共源輸出電容($V_{GS}=0\text{V}, V_{DS}=75\text{V}, f=1\text{MHz}$)	C_{OSS}	—	—	1010	pF
Total Gate Charge 柵極電荷密度 ($V_{DS}=120\text{V}, I_D=60\text{A}, V_{GS}=10\text{V}$)	Q_g	—	95	—	nC
Gate Source Charge 柵源電荷密度 ($V_{DS}=120\text{V}, I_D=60\text{A}, V_{GS}=10\text{V}$)	Q_{gs}	—	25	—	nC
Gate Drain Charge 柵漏電荷密度 ($V_{DS}=120\text{V}, I_D=60\text{A}, V_{GS}=10\text{V}$)	Q_{gd}	—	30	—	nC
Turn-ON Time 開啓時間 ($V_{DS}=75\text{V}, I_D=60\text{A}, R_{GEN}=6\Omega, V_{GS}=10\text{V}$)	$t_{(on)}$	—	20	—	ns
Turn-OFF Time 關斷時間 ($V_{DS}=75\text{V}, I_D=60\text{A}, R_{GEN}=6\Omega, V_{GS}=10\text{V}$)	$t_{(off)}$	—	105	—	ns



Dimension 外形封裝尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.470	4.670	0.176	0.184
A1	2.520	2.820	0.099	0.111
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
E1	12.060	12.460	0.475	0.491
e	2.540TYPE		0.100TYPE	
e1	4.980	5.180	0.196	0.204
F	2.590	2.890	0.102	0.114
h	0.000	0.300	0.000	0.012
L	13.400	13.800	0.528	0.543
L1	3.560	3.960	0.140	0.156
Φ	3.735	3.935	0.147	0.155